



ALPHA & OMEGA
SEMICONDUCTOR

AOD4144/AOI4144/AOU4144

30V N-Channel MOSFET

SDMOS™

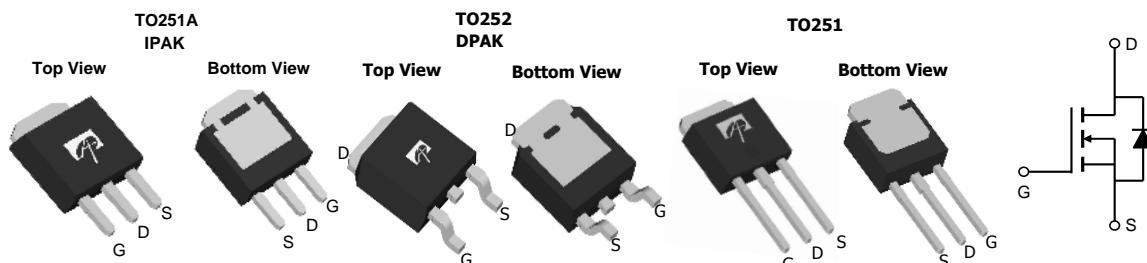
General Description

The AOD4144/AOI4144/AOU4144 is fabricated with SDMOS™ trench technology that combines excellent $R_{DS(ON)}$ with low gate charge and low Qrr. The result is outstanding efficiency with controlled switching behavior. This universal technology is well suited for PWM, load switching and general purpose applications.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	55A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 8mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 14mΩ

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	55	A
$T_C=100^\circ C$		42	
Pulsed Drain Current ^C	I_{DM}	110	
Continuous Drain Current	I_{DSM}	13	A
$T_A=70^\circ C$		10	
Avalanche Current ^C	I_{AS}, I_{AR}	30	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}, E_{AR}	45	mJ
Power Dissipation ^B	P_D	50	W
$T_C=100^\circ C$		25	
Power Dissipation ^A	P_{DSM}	2.3	W
$T_A=70^\circ C$		1.4	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	18	22	°C/W
Maximum Junction-to-Ambient ^{A D}		44	55	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	2.4	3	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			10 50	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.2	1.8	2.4	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	110			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$ $T_J=125^\circ\text{C}$		6.7 10	8 12	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		11	14	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		40		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current ^G				55	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$	950	1190	1430	pF
C_{oss}	Output Capacitance		150	220	290	pF
C_{rss}	Reverse Transfer Capacitance		80	130	180	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	0.4	0.9	1.4	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, I_D=20\text{A}$	18	23	28	nC
$Q_g(4.5\text{V})$	Total Gate Charge		9	11	13	nC
Q_{gs}	Gate Source Charge		2.4	3	3.6	nC
Q_{gd}	Gate Drain Charge		3.6	6	8.4	nC
$t_{\text{D(on)}}$	Turn-On DelayTime	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, R_L=0.75\Omega, R_{\text{GEN}}=3\Omega$		7		ns
t_r	Turn-On Rise Time			10		ns
$t_{\text{D(off)}}$	Turn-Off DelayTime			22		ns
t_f	Turn-Off Fall Time			5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	7.8	9.8	12	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	14	17.6	21	nC

A. The value of R_{0JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on R_{0JA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{0JA} is the sum of the thermal impedance from junction to case R_{0JC} and case to ambient.

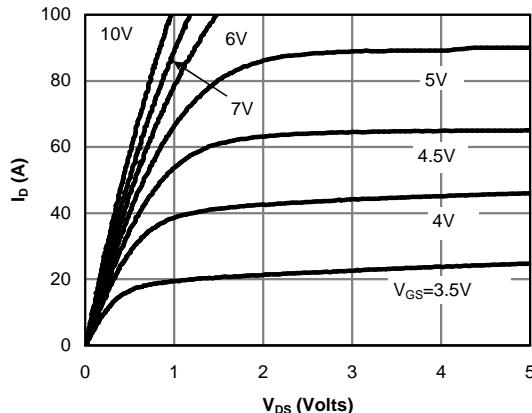
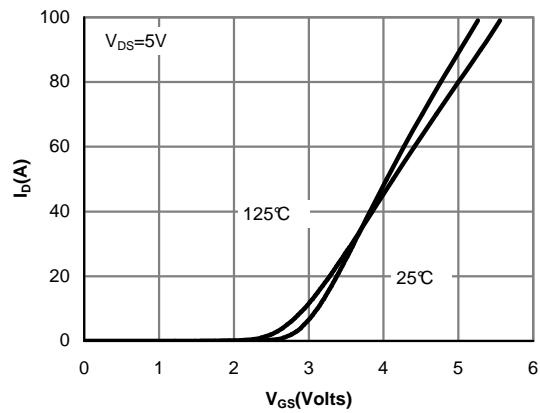
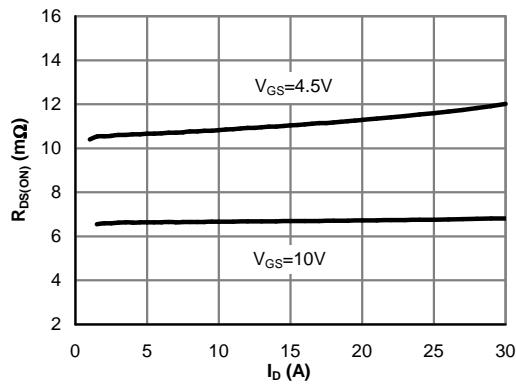
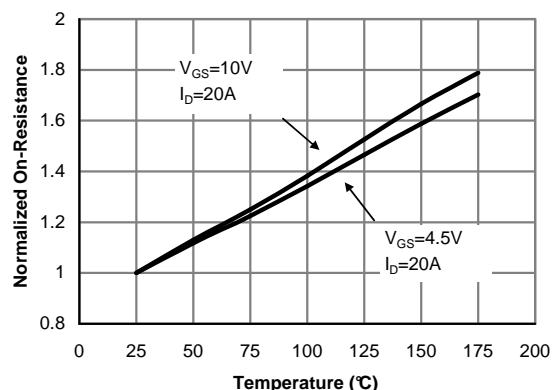
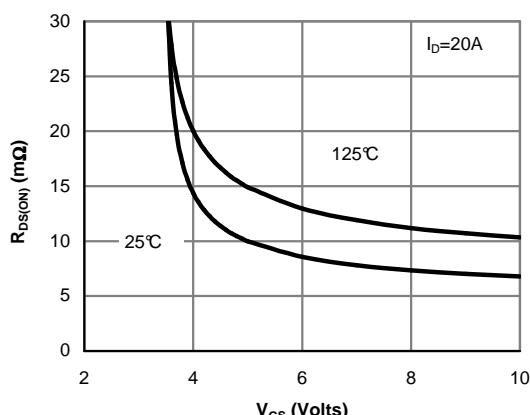
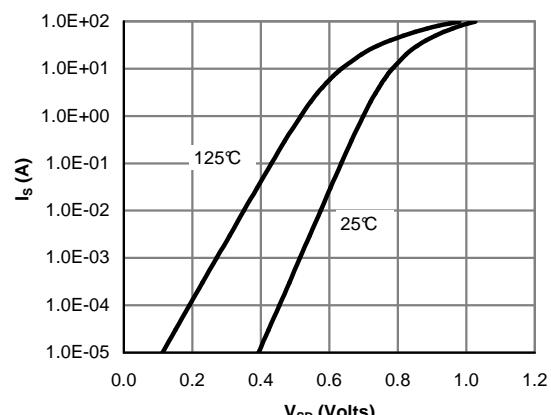
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

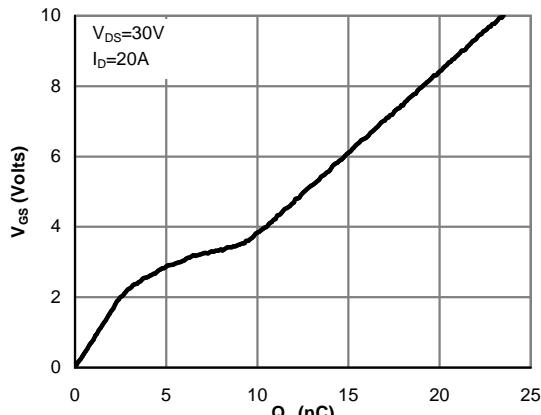
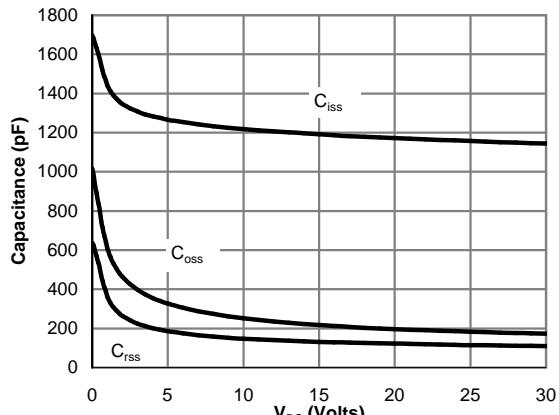
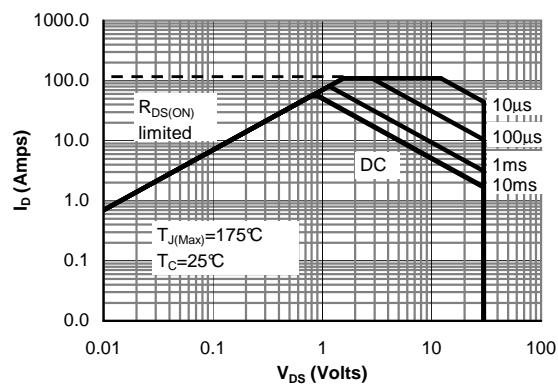
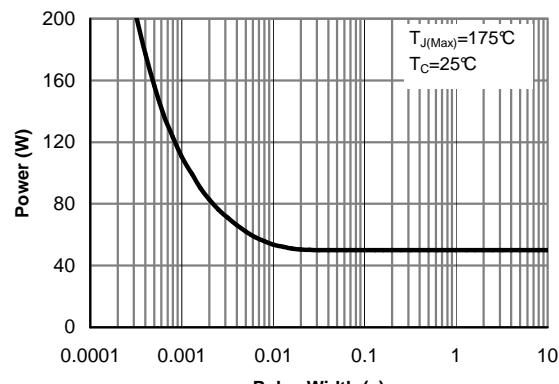
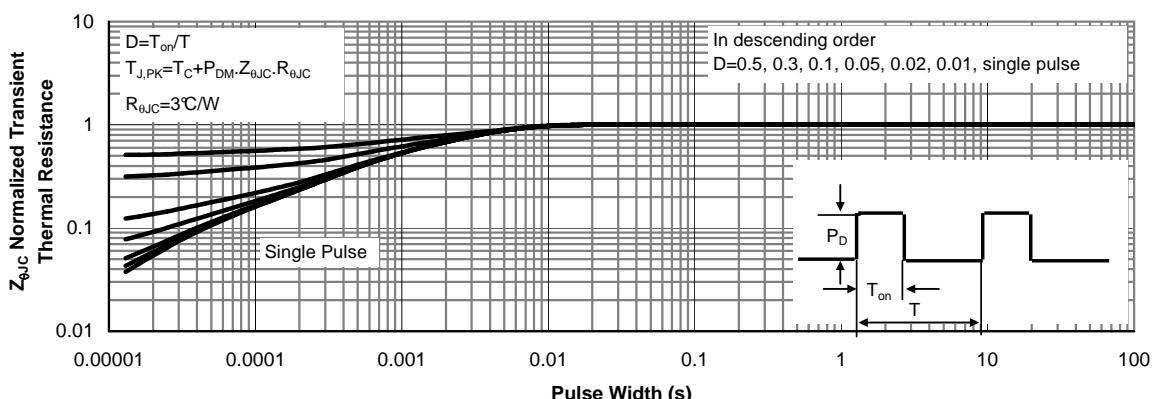
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

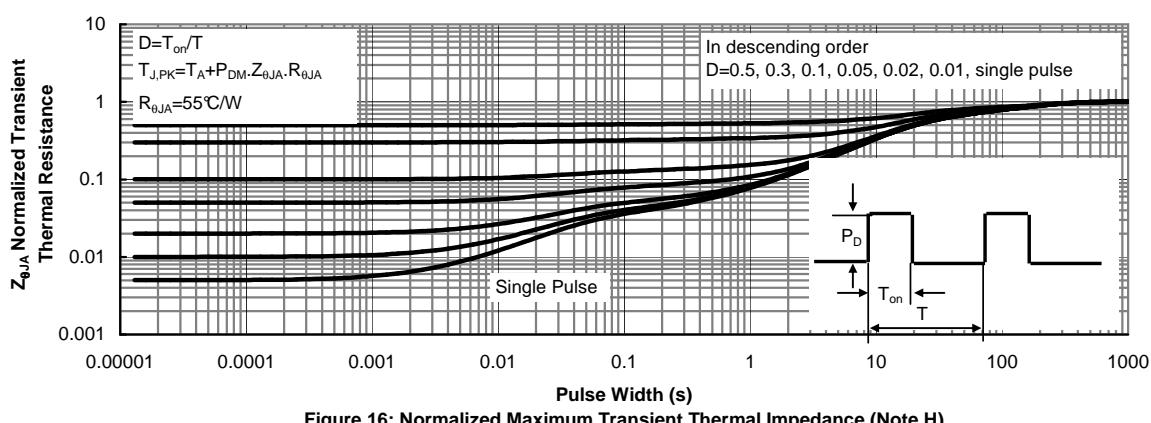
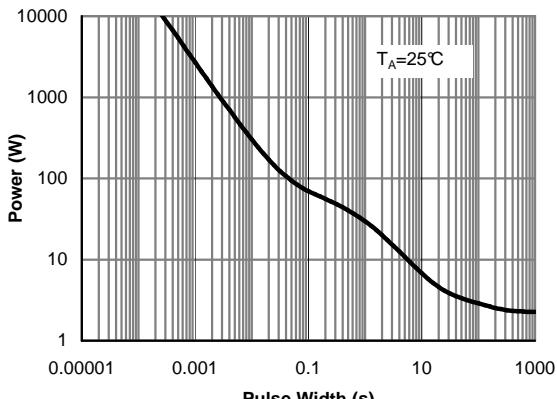
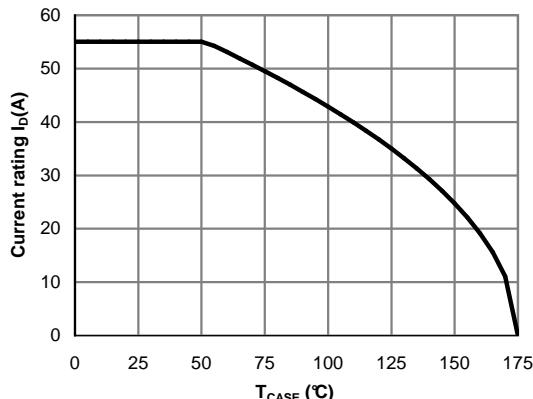
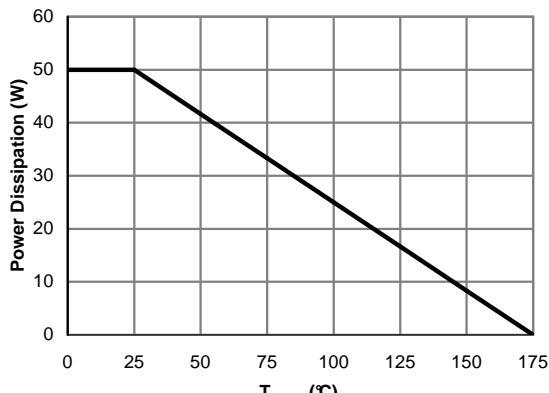
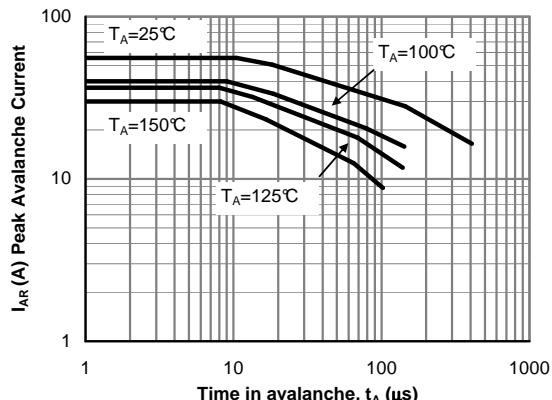
G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


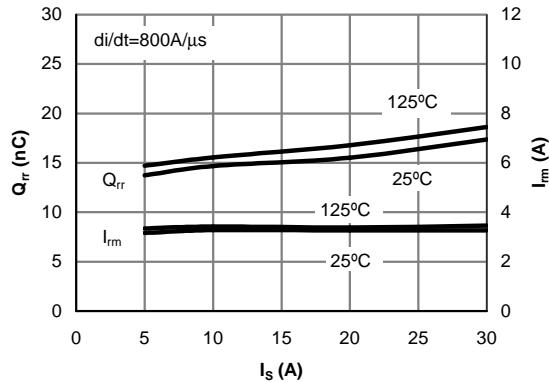
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Figure 17: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

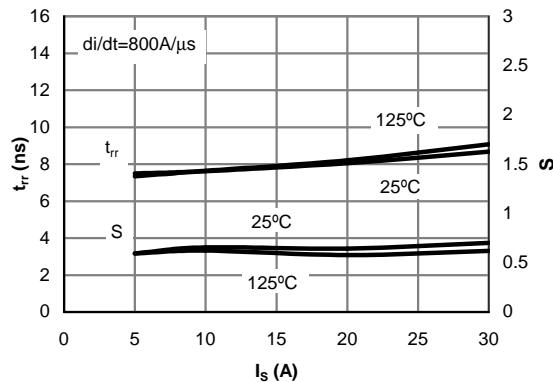


Figure 18: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current

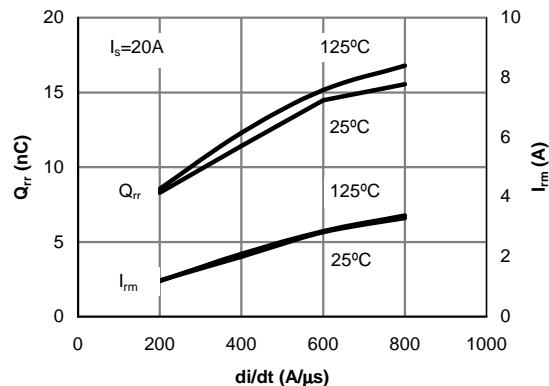


Figure 19: Diode Reverse Recovery Charge and Peak Current vs. $\frac{di}{dt}$

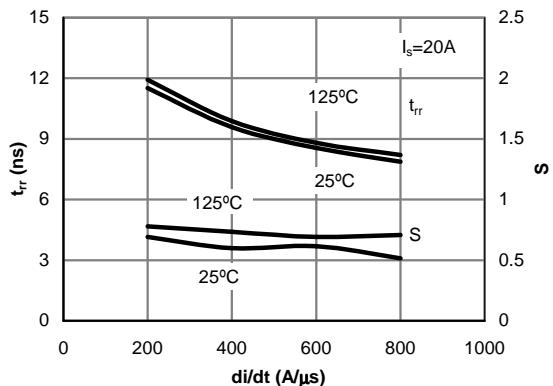
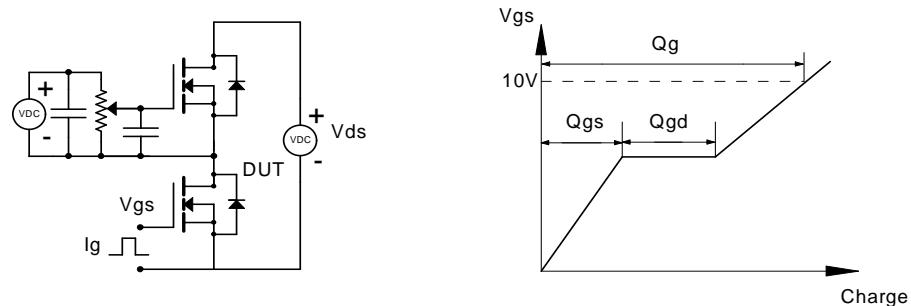
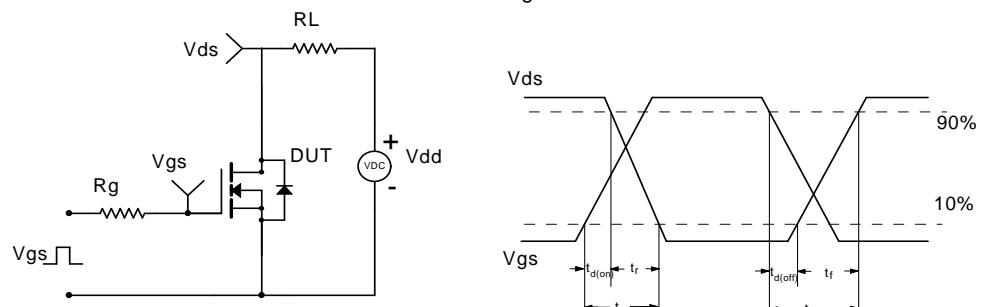
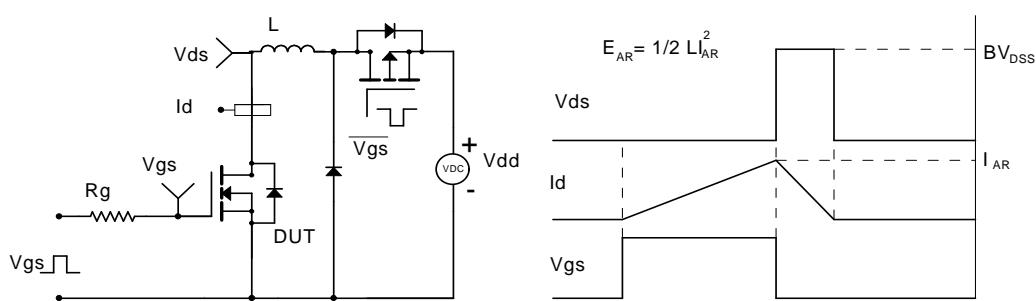


Figure 20: Diode Reverse Recovery Time and Softness Factor vs. $\frac{di}{dt}$

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms
